

## LOW-POWER CAN TRANSCEIVER WITH BUS WAKE-UP

Check for Samples: SN65HVD1040-HT

#### **FEATURES**

- Improved Drop-in Replacement for the TJA1040
- ±12 kV ESD Protection
- Low-Current Standby Mode with Bus Wake-up:
   5 μA Typical
- Bus-Fault Protection of –27 V to 40 V
- Rugged Split-Pin Bus Stability
- Dominant Time-Out Function
- Thermal Shutdown Removed
- Power-Up/Down Glitch-Free Bus Inputs and Outputs
  - High Input Impedance with Low V<sub>CC</sub>
  - Monotonic Outputs During Power Cycling
- DeviceNet Vendor ID # 806

#### **APPLICATIONS**

- Down-Hole Drilling
- High Temperature Environments
- Vibration/Modal Analysis
- Multi-Channel Data Acquisition
- Acoustics/Dynamic Strain Gauges
- Pressure Sensors

## SUPPORTS EXTREME TEMPERATURE APPLICATIONS

- Controlled Baseline
- One Assembly/Test Site
- · One Fabrication Site
- Available in Extreme (-55°C/210°C)
   Temperature Range (1)
- Extended Product Life Cycle
- Extended Product-Change Notification
- Product Traceability
- Texas Instruments high temperature products utilize highly optimized silicon (die) solutions with design and process enhancements to maximize performance over extended temperatures. All devices are characterized and qualified for 1000 hours continuous operating life at maximum rated temperature.

(1) Custom temperature ranges available

#### DESCRIPTION

The SN65HVD1040 meets or exceeds the specifications of the ISO 11898 standard for use in applications employing a Controller Area Network (CAN). As CAN transceivers, these devices provide differential transmit and receive capability for a CAN controller at signaling rates of up to 1 megabit per second (Mbps). (2)

Designed for operation in especially harsh environments, the device features  $\pm 12$  kV ESD protection on the bus and split pins, cross-wire, overvoltage and loss of ground protection from -27 to 40 V, a -12 V to 12 V common-mode range, and will withstand voltage transients from -200 V to 200 V according to ISO 7637.

The STB input (pin 8) selects between two different modes of operation; high-speed or low-power mode. The high-speed mode of operation is selected by connecting STB to ground.

If a high logic level is applied to the STB pin of the SN65HVD1040, the device enters a low-power bus-monitor standby mode. While the SN65HVD1040 is in the low-power bus-monitor standby mode, a dominant bit greater than 5 µs on the bus is passed by the bus-monitor circuit to the receiver output. The local protocol controller may then reactivate the device when it needs to transmit to the bus.

A dominant-time-out circuit in the SN65HVD1040 prevents the driver from blocking network communication during a hardware or software failure. The time-out circuit is triggered by a falling edge on TXD (pin 1). If no rising edge is seen before the time-out constant of the circuit expires, the driver is disabled. The circuit is then reset by the next rising edge on TXD.

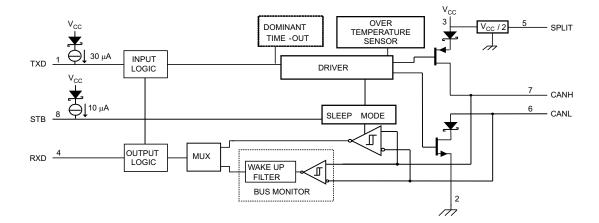
(2) The signaling rate of a line is the number of voltage transitions that are made per second expressed in the units bps (bits per second).

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



The SPLIT output (pin 5) is available on the SN65HVD1040 as a  $V_{\rm CC}/2$  common-mode bus voltage bias for a split-termination network.

The SN65HVD1040 is characterized for operation from -55°C to 210°C.







This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## Table 1. ORDERING INFORMATION<sup>(1)</sup>

T <sub>J</sub>	PACKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING
FF°C to 240°C	KGD (bare die)	SN65HVD1040SKGD3	NA
−55°C to 210°C	HKQ	SN65HVD1040SHKQ	HVD1040SHKQ
–55°C to 175°C	D	SN65HVD1040HD	H1040

<sup>(1)</sup> For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI Web site at www.ti.com.

#### **BARE DIE INFORMATION**

	DIE THICKNESS	BACKSIDE FINISH	BACKSIDE POTENTIAL	BOND PAD METALLIZATION COMPOSITION	BOND PAD THICKNESS
Ī	15 mils.	Silicon with backgrind	Floating	CuNiPd	15 microns

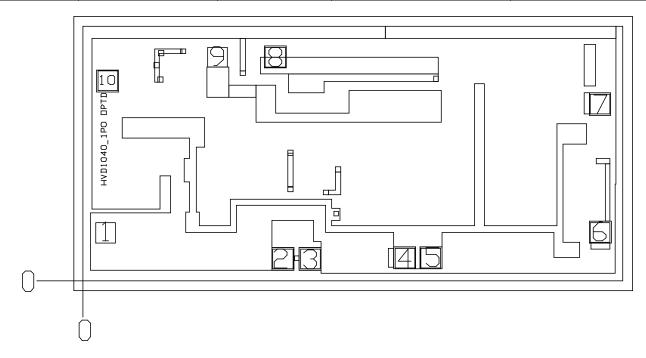


Table 2. BOND PAD COORDINATES (µm)

DESCRIPTION	PAD NUMBER	X MIN	Y MIN	X MAX	Y MAX	PAD SIZE X	PAD SIZE Y
TXD	1	53.64	162	137.7	246.06	84.06	84.06
GND	2	804.06	50.85	888.12	134.91	84.06	84.06
GND	3	920.07	50.85	1004.13	134.91	84.06	84.06
Vcc	4	1320.21	54.18	1404.27	138.24	84.06	84.06
Vcc	5	1431.09	54.18	1515.15	138.24	84.06	84.06
RXD	6	2148.75	164.34	2232.81	248.4	84.06	84.06
SPLIT	7	2147.4	707.49	2231.46	791.55	84.06	84.06
CANL	8	771.93	907.38	855.99	991.44	84.06	84.06
CANH	9	527.31	907.38	611.37	991.44	84.06	84.06
STB	10	62.28	806.13	146.34	890.19	84.06	84.06

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#### ABSOLUTE MAXIMUM RATINGS(1)

				VALUE				
V <sub>CC</sub>	Supply voltage (2)			–0.3 V to 7 V				
$V_{I(bus)}$	Voltage range at any bu	s terminal (CANH, CANL, SPLI	Τ)	–27 V to 40 V				
I <sub>O(OUT)</sub>	Receiver output current			-20 mA to 20 mA				
	Voltage input, transient p	Voltage input, transient pulse <sup>(3)</sup> , (CANH, CANL, SPLIT)						
	IEC Contact Discharge	(IEC 61000-4-2)	Bus terminals vs GND	±6 kV				
	Lluman hadu madal	JEDEC Standard 22,	Bus terminals vs GND	±12 kV				
ESD	Human body model	Test Method A114-C.01	All pins	±4 kV				
	Field-Induced-Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1 kV				
	Machine model	ANSI/ESDS5.2-1996		±200 V				
IEC			Bus terminals vs GND	±6 kV				
$V_{I}$	Voltage input range (TX	D, STB)		–0.5 V to 6 V				
TJ	Junction temperature			-55°C to 210°C				

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## THERMAL CHARACTERISTICS FOR HKQ PACKAGE

over operating free-air temperature range (unless otherwise noted)

	PARAME	TER	MIN	TYP	MAX	UNIT
0	lunction to coop thormal registance	to ceramic side of case			5.7	°C/W
₽ <sup>JC</sup>	Junction-to-case thermal resistance	to top of case lid (metal side of case)			13.7	C/VV

#### THERMAL INFORMATION FOR D PACKAGE

		SN65HVD1040	
	THERMAL METRIC <sup>(1)</sup>	D	UNITS
		8 PINS	
$\theta_{JA}$	Junction-to-ambient thermal resistance (2)	91.9	
$\theta_{JCtop}$	Junction-to-case (top) thermal resistance (3)	39.9	
$\theta_{JB}$	Junction-to-board thermal resistance <sup>(4)</sup>	40.6	90044
$\Psi_{JT}$	Junction-to-top characterization parameter <sup>(5)</sup>	3.9	°C/W
ΨЈВ	Junction-to-board characterization parameter <sup>(6)</sup>	39.6	
$\theta_{JCbot}$	Junction-to-case (bottom) thermal resistance (7)	N/A	

- (1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter, ψ<sub>JT</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter, ψ<sub>JB</sub>, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ<sub>JA</sub>, using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

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<sup>(2)</sup> All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

<sup>(3)</sup> Tested in accordance with ISO 7637, test pulses 1, 2, 3a, 3b, 5, 6 & 7.



## **RECOMMENDED OPERATING CONDITIONS**

			$T_{\rm J} = -58$	5°C to 12	5°C	$T_{\rm J} = -58$	5°C to 17	5°C	$T_J = -$	55°C to 21	0°C	UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	MIN	NOM	MAX	UNIT
$V_{CC}$	Supply voltage		4.75		5.25	4.75		5.25	4.75		5.25	V
$V_{IC}$ or	Voltage at any bus or common mode)	terminal (separately	-12 <sup>(1)</sup>		12	-12 <sup>(1)</sup>		12	-12 <sup>(1)</sup>		12	٧
V <sub>IH</sub>	High-level input voltage	TVD CTD	2		5.25	2		5.25	2		5.25	٧
V <sub>IL</sub>	Low-level input voltage	TXD, STB	0		0.8	0		0.8	0		0.8	V
$V_{ID}$	Differential input vo	Itage	-6		6	-6	6		-6		6	V
	High-level output	Driver	-70			-70			-70			A
I <sub>OH</sub>	current	Receiver	-2			-2			-2			mA
	Low-level output	Driver			70			70			70	A
I <sub>OL</sub>	current	Receiver			2			2			2	mA
t <sub>SS</sub>	Maximum pulse width to remain in standby				0.7			0.7			0.7	μs
$T_J$	Junction temperatur	re	-55		125	<b>–</b> 55		175	<b>–</b> 55		210	°C

<sup>(1)</sup> The algebraic convention, in which the least positive (most negative) limit is designated as minimum is used in this data sheet.

## **SUPPLY CURRRENT**

over operating free-air temperature range (unless otherwise noted)

	PARAMET	ED.	TEST CONDITIONS	$T_J = -55^{\circ}\text{C to } 125^{\circ}\text{C}$ $T_J = -55^{\circ}\text{C to } 175^{\circ}\text{C}$			$T_{\rm J} = -58$	5°C to 2	10°C	UNIT			
	PARAMEI	EK	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNII
		Domina nt	$V_I = 0 \text{ V}, 60 \Omega \text{ Load},$ STB at 0 V		50	70		50	70		50	70	A
I <sub>CC</sub>	Supply current, V <sub>CC</sub>	Recessi ve	$V_I = V_{CC}$ , STB at 0 V		6	10		6	10		6	10	mA
	•66	Standby	STB at VCC, VI = VCC		5	12		5	20		5	50	μΑ

## **DEVICE SWITCHING CHARACTERISTICS**

over recommended operating conditiions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	T <sub>J</sub> = -	55°C to 1	25°C	$T_{\rm J} = -5$	5°C to 17	75°C	$T_{\rm J} = -5$	5°C to 2	10°C	UNIT
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t <sub>loop</sub>	Total loop delay, driver input to receiver output, Recessive to Dominant	STB at 0 V.	90		230	90		325	90		450	
t <sub>loop</sub> 2	Total loop delay, driver input to receiver output, Dominant to Recessive	See Figure 10	90		230	90		325	90		450	ns

Product Folder Links: SN65HVD1040-HT



#### **DRIVER ELECTRICAL CHARACTERISTICS**

over recommended operating conditiions (unless otherwise noted)

	ADAMETE	D	TEST CONDITIONS	$T_{\rm J} = -5$	5°C to 12	5°C	$T_{\rm J} = -5$	55°C to 17	75°C	$T_J =$	-55°C to 2	10°C	UNIT
P	ARAMETE	ĸ	1EST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	MIN	TYP <sup>(1)</sup>	MAX	MIN	TYP <sup>(1)</sup>	MAX	UNII
V	Bus output	CAN H	V <sub>I</sub> = 0 V, STB at 0 V, R <sub>L</sub> =	2.9	3.4	4.5	2.9	3.4	4.6	2.9	3.4	4.6	V
V <sub>O(D)</sub>	voltage (Domina nt)	CANL	60 Ω, See Figure 2 and Figure 3	0.8		1.75	0.8		1.75	0.8		1.75	V
V <sub>O(R)</sub>	Bus output voltage (Recessive		V <sub>I</sub> = 3 V, STB at 0 V, See Figure 2 and Figure 3	2	2.5	3	2	2.5	3	2	2.5 3		V
Vo	Bus output voltage (S		$R_L = 60 \Omega$ , STB at $V_{CC}$ , See Figure 2 and Figure 3	-0.1		0.1	-0.125		0.125	-0.15		0.15	V
V	Differentia voltage	l output	$V_I = 0 \text{ V}, R_L = 60 \Omega, \text{ STB}$ at 0 V, See Figure 2 and Figure 3, and Figure 4	1.5		3	1.5		3	1.5		3	V
V <sub>OD(D)</sub>	(Dominant	:)	$V_I = 0$ V, $R_L = 45 \Omega$ , STB at 0 V, See Figure 2 and Figure 3	1.4		3	1.4		3	1.4	3		V
$V_{SYM}$	Output syr (Dominant Recessive [ V <sub>O(CANH)</sub> V <sub>O(CANL)</sub> ]	or ()	STB at 0 V, See Figure 3 and Figure 14	0.9×V <sub>CC</sub>	V <sub>CC</sub>	1.1×V <sub>C</sub>	0.9×V <sub>CC</sub>	V <sub>cc</sub>	1.1×V <sub>C</sub>	0.9×V <sub>C</sub>	$V_{CC}$	1.2×V <sub>CC</sub>	V
V <sub>OD(R)</sub>	Differential output		$V_I = 3 \text{ V}, R_L = 60 \Omega, \text{ STB}$ at 0 V, See Figure 2 and Figure 3	-0.012		0.012	-0.014		0.017	-0.015		0.02	V
OD(II)			V <sub>I</sub> = 3 V, STB at 0 V, No Load	-0.5		0.05	-0.5		0.225	-0.75		0.8	
V <sub>OC(D)</sub>	Common-routput volt (Dominant	age	CTD at 0 V. Can Figure 0	2	2.3	3	2	2.3	3	2	2.3	3.1	V
V <sub>OC(pp</sub>	Peak-to-pe common-n output volt	node	STB at 0 V, See Figure 9		0.3			0.3			0.3		V
I <sub>IH</sub>	High-level current, TX input		V <sub>I</sub> at V <sub>CC</sub>	-2		2	-3		3	-3		3	μA
I <sub>IL</sub>	Low-level current, TX input		V <sub>I</sub> at 0 V	-50		-10	-50		-10	-50		-10	μΑ
I <sub>O(off)</sub>	Power-off Leakage o		V <sub>CC</sub> at 0 V, TXD at 5 V			1			180			600	μA
			V <sub>CANH</sub> = -12 V, CANL Open, See Figure 13	-120	-72		-120	-72		-130	-72		
l	Short-circu		V <sub>CANH</sub> = 12 V, CANL Open, See Figure 13		0.36	1		0.36	1		0.36	1.1	mA
'OS(ss)	steady-sta output cur	rent	V <sub>CANL</sub> = -12 V, CANH Open, See Figure 13	-1	-0.5		-1	-0.5		-1.1	-0.5		IIIA
			V <sub>CANL</sub> = 12 V, CANH Open, See Figure 13		71	120		71	120		71	130	
Co	Output capacitano	ce	See Input capacitance to ground in RECEIVER ELECTRICAL CHARACTERISTICS.										

<sup>(1)</sup> All typical values are at 25°C with a 5-V supply.



## **DRIVER SWITCHING CHARACTERISTICS**

over recommended operating conditions (unless otherwise noted)

	DADAMETED	TEST COMPITIONS	$T_{\rm J} = -5$	5°C to 12	25°C	$T_{\rm J} = -5$	5°C to 1	75°C	$T_{\rm J} = -5$	5°C to	210°C	
	PARAMETER	TEST CONDITIONS	MIN TYP MA				TYP	MAX	MIN	TYP	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low-to-high-level output		25	65	120	25	65	175	25	65	250	
t <sub>PHL</sub>	Propagation delay time, high-to-low-level output		25	45	120	25	45	175	25	45	250	
t <sub>sk(p)</sub>	Pulse skew ( t <sub>PHL</sub> - t <sub>PLH</sub>  )	STB at 0 V, See Figure 5			25		25				25	ns
t <sub>r</sub>	Differential output signal rise time			25			25			25		
t <sub>f</sub>	Differential output signal fall time			50			50			50		
t <sub>en</sub>	Enable time from silent mode to dominant	See Figure 8			11			14.5			18	μs
t <sub>dom</sub>	Dominant time-out	See Figure 11	300	450	700	300	450	700	300	450	700	μs



#### RECEIVER ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	DADAME	TED	TEST COMPLETONS	T <sub>J</sub> = -5	5°C to 1	25°C	$T_J = -$	55°C to	175°C	T <sub>J</sub> = -5	5°C to	210°C	LINUT
	PARAME	IEK	TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V <sub>IT+</sub>	Positive- going input threshold voltage		STB at 0 V, See Table 3		800	900		800	900		800	900	
V <sub>IT-</sub>	Negative- going input threshold voltage	High-speed mode	STB at U.V., See Table 3	500	650		500	650		500	650		mV
$V_{hys}$	Hysteresis voltage (V <sub>IT+</sub> – V <sub>IT-</sub> )		STB at V <sub>CC</sub>	100	125		70	125		70	125		
$V_{\text{IT}}$	Input threshold voltage	Standby mode	STB at V <sub>CC</sub>	500		1150	500		1300	400		1350	
$V_{OH}$	High-level ou	tput voltage	I <sub>O</sub> = -2 mA, See Figure 7	4	4.6		4	4.6		4	4.6		V
$V_{OL}$	Low-level out	put voltage	I <sub>O</sub> = 2 mA, See Figure 7		0.2	0.4		0.2	0.5		0.2	0.55	٧
$I_{\text{I(off)}}$	Power-off bus	s input current	CANH or CANL = 5 V, V <sub>CC</sub> at 0 V, TXD at 0 V			5			15			30	μΑ
I <sub>O(off)</sub>	Power-off RX current	D leakage	V <sub>CC</sub> at 0 V, RXD at 5 V			20			30			30	μΑ
Cı	Input capacita (CANH or CA	ance to ground,	TXD at 3 V, $V_1 = 0.4 \sin (4E6\pi t) + 2.5 V$		20			20			20		pF
C <sub>ID</sub>	Differential in	put capacitance	TXD at 3 V, V <sub>I</sub> = 0.4 sin (4E6πt)		10			10			10		pF
$R_{\text{ID}}$	Differential in	put resistance	TXD at 3 V, STD at 0 V	30		80	30		80	30		80	
R <sub>IN</sub>	Input resistar CANL)	ice, (CANH or	TXD at 3 V, STD at 0 V	15	30	40	15	30	40	15	30	40	kΩ
R <sub>I(m)</sub>	Input resistar [1 – (R <sub>IN (CANE</sub> 100%	ice matching H) / R <sub>IN (CANL)</sub> )] x	V <sub>CANH</sub> = V <sub>CANL</sub>	-3%	0%	3%	-5%	0%	5%	-12%	0%	12%	

#### RECEIVER SWITCHING CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

	DADAMETED	TEST CONDITIONS	$T_J = -5$	$T_J = -55^{\circ}C$ to 175°C			$T_J = -55$ °C to 210°C			UNIT		
	PARAMETER	TEST CONDITIONS	MIN TYP MAX			MIN	TYP	MAX	MIN	TYP	MAX	UNII
t <sub>pLH</sub>	Propagation delay time, low-to-high-level output		60	100	130	60	100	200	60	100	200	
t <sub>pHL</sub>	Propagation delay time, high- to-low-level output	STB at 0 V, TXD at 3 V, See Figure 7	45	70	130	45	70	200	45	70	200	ns
t <sub>r</sub>	Output signal rise time			8			8			8		
t <sub>f</sub>	Output signal fall time			8			8			8		
t <sub>BUS</sub>	Dominant time required on bus for wake-up from standby <sup>(1)</sup>	STB at V <sub>CC</sub> Figure 12	0.7		5	1.0		5.1	1.45		5.25	μs

<sup>(1)</sup> The device under test shall not signal a wake-up condition with dominant pulses shorter than t<sub>BUS</sub> (min) and shall signal a wake-up condition with dominant pulses longer than t<sub>BUS</sub> (max). Dominant pulses with a length between t<sub>BUS</sub> (min) and t<sub>BUS</sub> (max) may lead to a wake-up.

## **SPLIT-PIN CHARACTERISTICS**

over recommended operating conditiions (unless otherwise noted)

	DADAMETED	TEST	T <sub>J</sub> = -55°C to 125°C			$T_{\rm J} = -1$	55°C to 17	5°C	T <sub>J</sub> = -55°C to 210°C				
	PARAMETER	CONDITIONS		TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNIT	
Vo	Output voltage	–500 μA < I <sub>O</sub> < 500 μA	0.3×V <sub>CC</sub>	0.5×V <sub>CC</sub>	0.7×V <sub>CC</sub>	0.28×V <sub>CC</sub>	0.5×V <sub>CC</sub>	0.7xV <sub>CC</sub>	0.28×V <sub>C</sub>	0.5×V <sub>C</sub>	0.7xV <sub>CC</sub>	V	
I <sub>O(st</sub> b)	Standby mode leakage current	STB at 2 V, -12 V ≤ V <sub>O</sub> ≤ 12 V	-5		5	-7		7	-15		15	μА	

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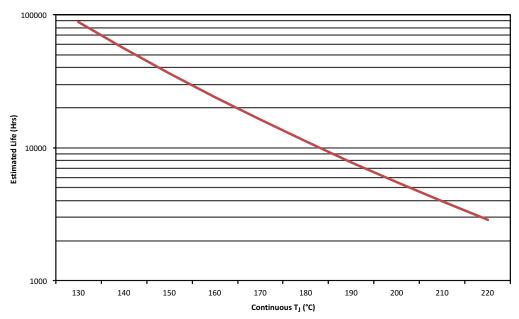
Product Folder Links: SN65HVD1040-HT



#### STB-PIN CHARACTERISTICS

over recommended operating conditiions (unless otherwise noted)

PARAMETER		TEST	T <sub>J</sub> = -	55°C to 12	25°C	T <sub>J</sub> = -5	55°C to 175°C	T <sub>J</sub> = -5	55°C to 21	0°C	LINUT
	PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP MAX	MIN	TYP	MAX	UNIT
I <sub>IH</sub>	High level input current	STB at 2 V	-10		0	-10	0	-10		0	μA
$I_{\rm IL}$	Low level input current	STB at 0 V	-10		0	-10	0	-10		0	μΑ



- A. See datasheet for absolute maximum and minimum recommended operating conditions.
- B. Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).
- C. The predicted operating lifetime vs. junction temperature is based on reliability modeling using electromigration as the dominant failure mechanism affecting device wear out for the specific device process and design characteristics.

Figure 1. SN65HVD1040-HT Operating Life Derating Chart



#### PARAMETER MEASUREMENT INFORMATION

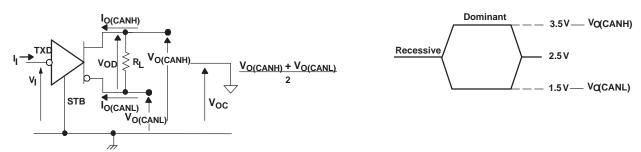


Figure 2. Driver Voltage, Current, and Test Definition

Figure 3. Bus Logic State Voltage Definitions

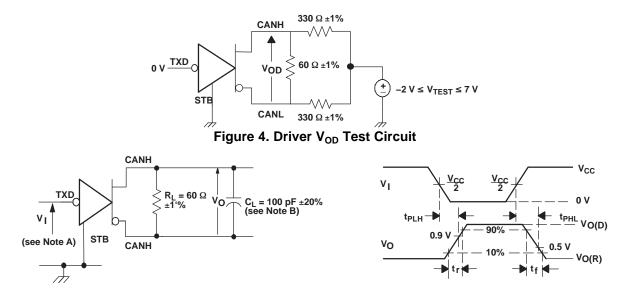


Figure 5. Driver Test Circuit and Voltage Waveforms

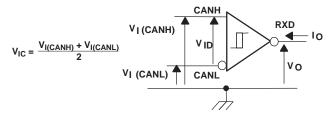
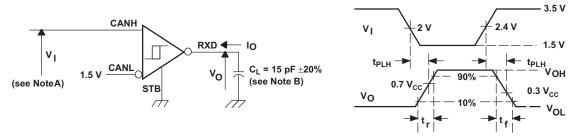


Figure 6. Receiver Voltage and Current Definitions



#### PARAMETER MEASUREMENT INFORMATION (continued)



- A. The input pulse is supplied by a generator having the following characteristics: PRR  $\leq$  125 kHz, 50% duty cycle,  $t_r \leq$  6 ns,  $t_f \leq$  6ns,  $Z_O = 50 \Omega$ .
- B. C<sub>1</sub> includes instrumentation and fixture capacitance within ±20%.

Figure 7. Receiver Test Circuit and Voltage Waveforms

**INPUT OUTPUT** R  $V_{CANH}$ VCANL  $|V_{ID}|$ -11.1 V -12 V 900 mV L  $V_{OL}$ 12 V 11.1 V 900 mV L -6 V -12 V 6 V L 12 V 6 V 6 V L -11.5 V -12 V 500 mV Н  $V_{OH}$ 12 V 11.5 V 500 mV Н -12 V -6 V 6 V Н 6 V 12 V 6 V Н Χ Open Open Н

**Table 3. Differential Input Voltage Threshold Test** 

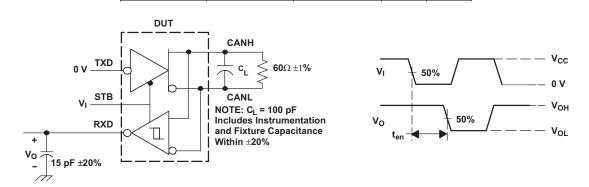
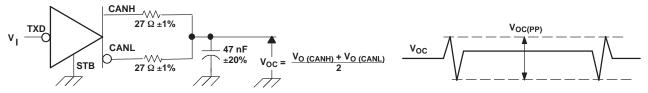


Figure 8.  $t_{en}$  Test Circuit and Voltage Waveforms

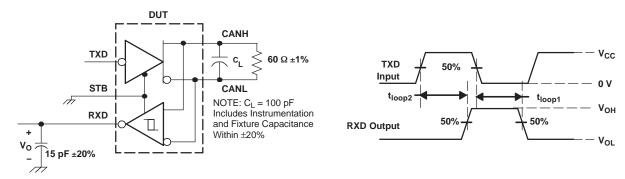


A. All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator having the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

Figure 9. Peak-to-Peak Common Mode Output Voltage Test and Waveform

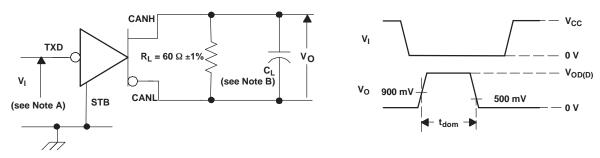
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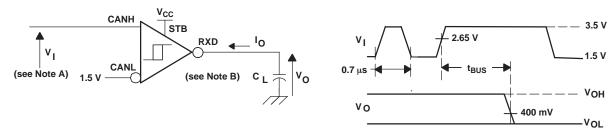
A. All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator with the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 125 kHz, 50% duty cycle.

Figure 10. t<sub>loop</sub> Test Circuit and Voltage Waveforms



- A. All  $V_1$  input pulses are from 0 V to  $V_{CC}$  and supplied by a generator with the following characteristics:  $t_r$  or  $t_f \le 6$  ns. Pulse Repetition Rate (PRR) = 500 Hz, 50% duty cycle.
- B.  $C_L = 100 \text{ pF}$  includes instrumentation and fixture capacitance within  $\pm 20\%$ .

Figure 11. Dominant Time-Out Test Circuit and Waveform



- A. For  $V_I$  bit width  $\leq 0.7 \ \mu s$ ,  $V_O = V_{OH}$ . For  $V_I$  bit width  $\geq 5 \ \mu s$ ,  $V_O = V_{OL}$ .  $V_I$  input pulses are supplied from a generator with the following characteristics;  $t_r$  or  $t_f \leq 6$  ns. Pulse Repetition Rate (PRR) = 50 Hz, 30% duty cycle.
- B.  $C_L = 15 \text{ pF}$  includes instrumentation and fixture capacitance within  $\pm 20\%$ .

Figure 12. t<sub>BUS</sub> Test Circuit and Waveform



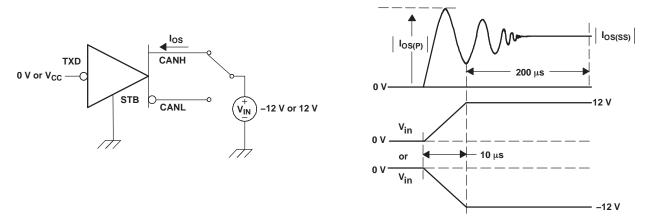


Figure 13. Driver Short-Circuit Current Test and Waveform

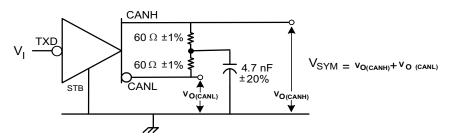


Figure 14. Driver Output Symmetry Test Circuit



#### **DEVICE INFORMATION**

Table 4. DRIVER FUNCTION TABLE(1)

INP	UTS	OUTI	PUTS	BUS STATE
TXD	STB	STB CANH CANL		
L	L	L H		DOMINANT
Н	L	Z	Z	RECESSIVE
Open	Х	Z	Z	RECESSIVE
Х	H or Open	Z	Z	RECESSIVE

(1) H = high level; L = low level; X = irrelevant; Z = high impedance

Table 5. RECEIVER FUNCTION TABLE<sup>(1)</sup>

DIFFERENTIAL INPUTS V <sub>ID</sub> = CANH - CANL	STB	OUTPUT RXD	BUS STATE
V <sub>ID</sub> ≥ 0.9 V	L	L	DOMINANT
V <sub>ID</sub> ≥ 1.15 V	H or Open	L	DOMINANT
$0.5 \text{ V} < \text{V}_{\text{ID}} < 0.9 \text{ V}$	X	?	?
V <sub>ID</sub> ≤ 0.5 V	Х	Н	RECESSIVE
Open	Х	Н	RECESSIVE

(1) H = high level; L = low level; X = irrelevant; ? = indeterminate; Z = high impedance



## **DEVICE INFORMATION**

Table 6. Parametric Cross Reference With the TJA1040

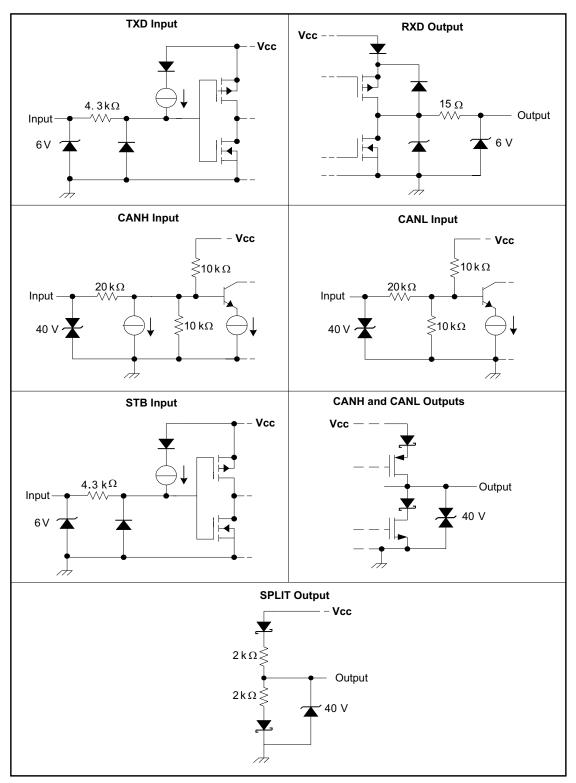
TJA1040 <sup>(1)</sup>	PARAMETER	HVD10xx				
	TJA1040 DRIVER SECTION					
V <sub>IH</sub>	High-level input voltage	Recommended V <sub>IH</sub>				
V <sub>IL</sub>	Low-level input voltage	Recommended V <sub>IL</sub>				
I <sub>IH</sub>	High-level input current	Driver I <sub>IH</sub>				
I <sub>IL</sub>	Low-level input current	Driver I <sub>IL</sub>				
	TJA1040 BUS SECTION					
V <sub>th(dif)</sub>	Differential input voltage	Receiver $V_{\text{IT}}$ and recommended $V_{\text{ID}}$				
V <sub>hys(dif)</sub>	Differential input hysteresis	Receiver V <sub>hys</sub>				
V <sub>O(dom)</sub>	Dominant output voltage	Driver V <sub>O(D)</sub>				
V <sub>O(reces)</sub>	Recessive output voltage	Driver V <sub>O(R)</sub>				
$V_{i(dif)(th)}$	Differential input voltage	Receiver $V_{\text{IT}}$ and recommended $V_{\text{ID}}$				
V <sub>O(dif0(bus)</sub>	Differential bus voltage	Driver $V_{OD(D)}$ and $V_{OD(R)}$				
ILI	Power-off bus input current	Receiver I <sub>I(off)</sub>				
I <sub>O(SC)</sub>	Short-circuit output current	Driver I <sub>OS(SS)</sub>				
R <sub>i(cm)</sub>	CANH, CANL input resistance	Receiver R <sub>IN</sub>				
R <sub>i(def)</sub>	Differential input resistance	Receiver R <sub>ID</sub>				
R <sub>i(cm) (m)</sub>	Input resistance matching	Receiver R <sub>I (m)</sub>				
C <sub>i(cm)</sub>	Input capacitance to ground	Receiver C <sub>I</sub>				
C <sub>i(dif)</sub>	Differential input capacitance	Receiver C <sub>ID</sub>				
	TJA1040 RECEIVER SECTION					
I <sub>OH</sub>	High-level output current	Recommended I <sub>OH</sub>				
I <sub>OL</sub>	Low-level output current	Recommended I <sub>OL</sub>				
	TJA1040 SPLIT PIN SECTION					
Vo	Reference output voltage	Vo				
	TJA1040 TIMING SECTION					
t <sub>d(TXD-BUSon)</sub>	Delay TXD to bus active	Driver t <sub>PLH</sub>				
t <sub>d(TXD-BUSoff)</sub>	Delay TXD to bus inactive	Driver t <sub>PHL</sub>				
t <sub>d(BUSon-RXD)</sub>	Delay bus active to RXD	Receiver t <sub>PHL</sub>				
t <sub>d(BUSoff-RXD)</sub>	Delay bus inactive to RXD	Receiver t <sub>PLH</sub>				
t <sub>PD(TXD-RXD)</sub>	Prop delay TXD to RXD	Device t <sub>LOOP1</sub> and t <sub>LOOP2</sub>				
t <sub>d(stb-norm)</sub>	Enable time from standby to dominant	Driver t <sub>en</sub>				
	TJA1040 STB PIN SECTION					
V <sub>IH</sub>	High-level input voltage	Recommended V <sub>IH</sub>				
V <sub>IL</sub>	Low-level input voltage	Recommended V <sub>IL</sub>				
I <sub>IH</sub>	High-level input current	I <sub>IH</sub>				
I <sub>IL</sub>	Low-level input current	I <sub>IL</sub>				

<sup>(1)</sup> From TJA1040 Product Specification, Philips Semiconductors, 2003 February 19.

Product Folder Links: SN65HVD1040-HT

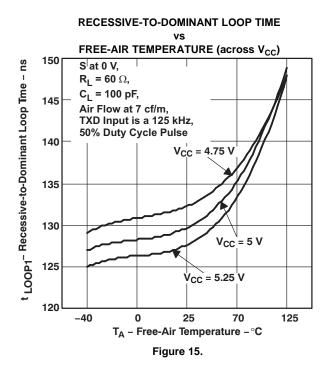


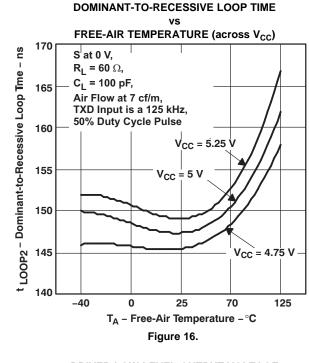
## **Equivalent Input and Output Schematic Diagrams**

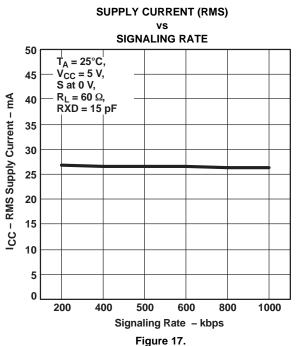


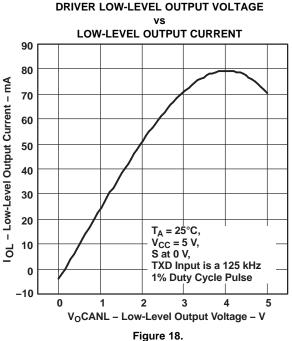


#### TYPICAL CHARACTERISTICS





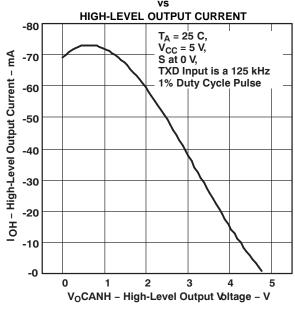






#### TYPICAL CHARACTERISTICS (continued)

## DRIVER HIGH-LEVEL OUTPUT VOLTAGE



#### Figure 19.

# DRIVER DIFFERENTIAL OUTPUT VOLTAGE vs FREE-AIR TEMPERATURE (across Vcc)

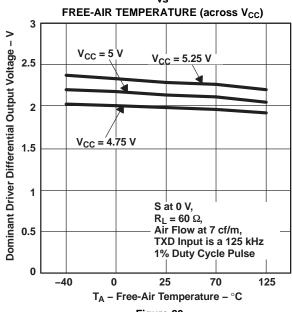


Figure 20.

#### **DRIVER OUTPUT CURRENT**

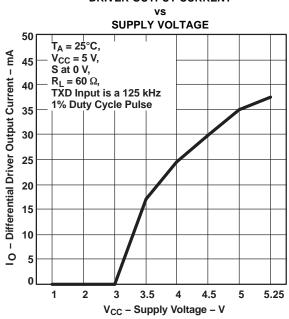


Figure 21.

#### **RECEIVER OUTPUT VOLTAGE**

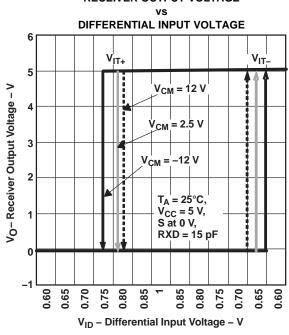


Figure 22.



## TYPICAL CHARACTERISTICS (continued)

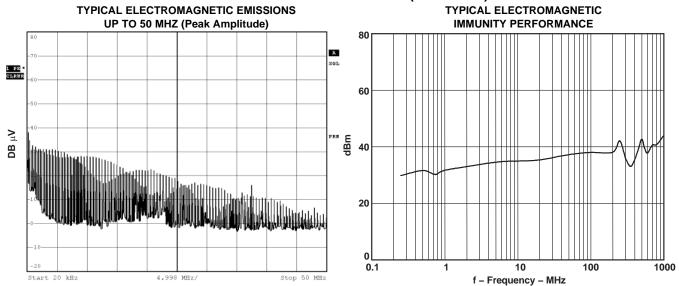


Figure 23. Frequency Spectrum of Common-Mode Emissions

Figure 24. Direct Power Injection (DPI) Response vs Frequency



#### **APPLICATION INFORMATION**

#### **CAN Basics**

The basics of arbitration require that the receiver at the sending node designate the first bit as dominant or recessive after the initial wave of the first bit of a message travels to the most remote node on a network and back again. Typically, this "sample" is made at 75% of the bit width, and within this limitation, the maximum allowable signal distortion in a CAN network is determined by network electrical parameters.

Factors to be considered in network design include the approximately 5 ns/m propagation delay of typical twisted-pair bus cable; signal amplitude loss due to the loss mechanisms of the cable; and the number, length, and spacing of drop-lines (stubs) on a network. Under strict analysis, variations among the different oscillators in a system also need to be accounted for with adjustments in signaling rate and stub and bus length. Table 7 lists the maximum signaling rates achieved with the SN65HVD1040 with several bus lengths of category 5, shielded twisted pair (CAT 5 STP) cable.

Table 7. Maximum Signaling Rates for Various Cable Lengths

Bus Length (m)	Signaling Rate (kbps)
30	1000
100	500
250	250
500	125
1000	62.5

The ISO 11898 Standard specifies a maximum bus length of 40 m and maximum stub length of 0.3 m with a maximum of 30 nodes. However, with careful design, users can have longer cables, longer stub lengths, and many more nodes to a bus. (Note: Non-standard application may come with a trade-off in signaling rate.) A large number of nodes requires a transceiver with high input impedance such as the HVD1040.

The Standard specifies the interconnect to be a single twisted-pair cable (shielded or unshielded) with 120  $\Omega$  characteristic impedance ( $Z_0$ ). Resistors equal to the characteristic impedance of the line terminate both ends of the cable to prevent signal reflections. Unterminated drop-lines connect nodes to the bus and should be kept as short as possible to minimize signal reflections.

Connectors, while not specified by the standard should have as little effect as possible on standard operating parameters such as capacitive loading. Although unshielded cable is used in many applications, data transmission circuits employing CAN transceivers are usually used in applications requiring a rugged interconnection with a wide common-mode voltage range. Therefore, shielded cable is recommended in these electronically harsh environments, and when coupled with the Standard's –2-V to 7-V common-mode range of tolerable ground noise, helps to ensure data integrity. The HVD1040 enhances the Standard's insurance of data integrity with an extended –12 V to 12 V range of common-mode operation.



## **PACKAGE OPTION ADDENDUM**

4-Feb-2021

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN65HVD1040HD	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-4-260C-72 HR	-55 to 175	H1040	Samples
SN65HVD1040SHKQ	ACTIVE	CFP	HKQ	8	25	RoHS & Green	AU	N / A for Pkg Type	-55 to 210	HVD1040S HKQ	Samples
SN65HVD1040SKGD3	ACTIVE	XCEPT	KGD	0	210	RoHS & Green	Call TI	N / A for Pkg Type	-55 to 210		Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## **PACKAGE OPTION ADDENDUM**

4-Feb-2021

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

#### OTHER QUALIFIED VERSIONS OF SN65HVD1040-HT:

Catalog: SN65HVD1040

Automotive: SN65HVD1040-Q1

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects

## **PACKAGE MATERIALS INFORMATION**

www.ti.com 5-Jan-2022

## **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65HVD1040HD	D	SOIC	8	75	505.46	6.76	3810	4
SN65HVD1040SHKQ	HKQ	CFP	8	25	506.98	26.16	6220	NA

## **PACKAGE OUTLINE**

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



## NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



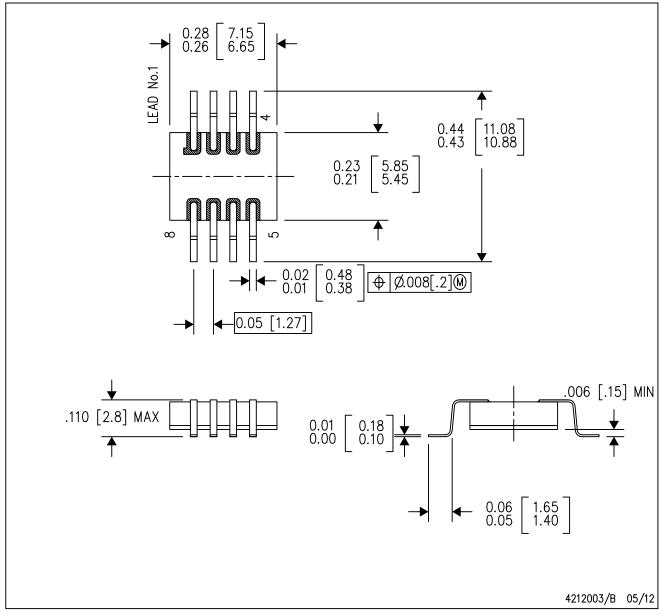
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



HKQ (R-CDFP-G8)

CERAMIC GULL WING



NOTES:

- All linear dimensions are in inches (millimeters).
- This drawing is subject to change without notice.
- This package can be hermetically sealed with a metal lid.
- D. The terminals will be gold plated.E. Lid is not connected to any lead.



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